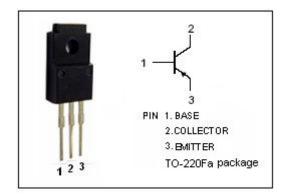
## **SPTECH Silicon PNP Power Transistor**

## 2SA1452

#### **DESCRIPTION**

- · Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= -0.4V(Max)@I<sub>C</sub>= -6A
- Good Linearity of h<sub>FE</sub>
- · High Switching Speed
- Complement to Type 2SC3710

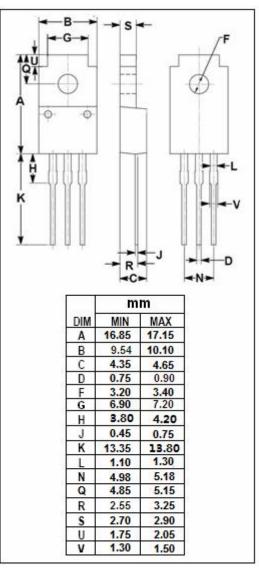


#### **APPLICATIONS**

• Designed for high current switching applications

#### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	-80	V	
V <sub>CEO</sub>	Collector-Emitter Voltage -80		V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
lc	Collector Current-Continuous	-12	А	
I <sub>B</sub>	Base Current-Continuous	-2	А	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C  30		W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Γ <sub>stg</sub> Storage Temperature Range -55~150 °C		$^{\circ}$ C	



1

## **SPTECH Silicon PNP Power Transistor**

2SA1452

0.5

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= -50mA ; I <sub>B</sub> = 0	-80			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A			-0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A			-1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -80V ; I <sub>E</sub> = 0			-10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -6V ; I <sub>C</sub> = 0			-10	μА
h <sub>FE-1</sub>	DC Current Gain	Ic= -1A ; Vc== -1V	70		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -6A ; V <sub>CE</sub> = -1V	40			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V;f <sub>test</sub> = 1MHz		400		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	Ic= -1A; Vc== -5V		50		MHz
Switching Times						
t <sub>on</sub>	Turn-on Time			0.3		μs
t <sub>stg</sub>	Storage Time	$I_{C}$ = -6A , $I_{B1}$ = - $I_{B2}$ = -0.3A, $V_{CC}$ = -30V, $R_{L}$ = 5 $\Omega$		1.0		μs

### ♦ h<sub>FE-1</sub> Classifications

Fall Time

0	Υ
70-140	120-240

μs

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